

Application No.: 10/625,234

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**AMENDMENTS TO THE CLAIMS**

Claim 1 (original): A semiconductor light emitting device, comprising:

a semiconductor substrate;

a stacked semiconductor structure formed on the semiconductor substrate;

a striped ridge structure; and

a semiconductor current confinement layer provided on a side surface of the striped ridge structure;

wherein the stacked semiconductor structure includes a first semiconductor clad layer, a semiconductor active layer, a second semiconductor clad layer, and a semiconductor etching stop layer;

wherein the striped ridge structure includes a third semiconductor clad layer, a semiconductor intermediate layer, and a semiconductor cap layer;

wherein the striped ridge structure is provided on the semiconductor etching stop layer;  
and

wherein an interface between the semiconductor current confinement layer and the semiconductor etching stop layer and an interface between the semiconductor current confinement layer and the striped ridge structure each have a content of impurities of less than  $1 \times 10^{17}/\text{cm}^3$ .

Claim 2 (original): A semiconductor light emitting device according to claim 1, wherein the impurities are carbon-based impurities.

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Claim 3 (original): A semiconductor light emitting device according to claim 1, wherein the impurities are oxygen-based impurities.

Claim 4 (original): A semiconductor light emitting device according to claim 1, wherein the impurities are carbon-based impurities and oxygen-based impurities.

Claims 5-20 (cancelled)

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